

Kmcsemiconductor
corporationK5001
K5002 K5003NPN
SILICON
TRANSISTOR**GENERAL DESCRIPTION**

Double-diffused, NPN Silicon transistors designed for low-level, low-noise UHF and VHF amplifier applications. Exceptional performance in Converter and Oscillator circuitry in the UHF range.

A modified TO-72 package having a fourth lead connected to the case for grounding and shielding purposes is used. All active elements are isolated from the case.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Operating Junction Temperature	200°C Maximum
Storage Temperature	-55°C to +200°C

Maximum Power Dissipation at 25°C Amb.	200mw
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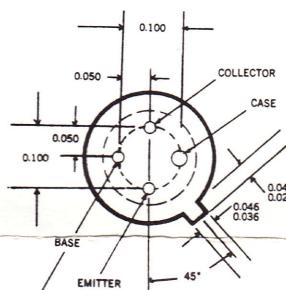
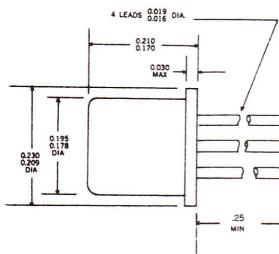
Maximum Voltages

V _{cbo} Collector to Base Voltage	25 Volts
V _{ceo} Collector to Emitter Voltage	12 volts
V _{ebo} Emitter to Base Voltage	2.5 volts

Derate:

1.72 mw/°C for 25°C Case

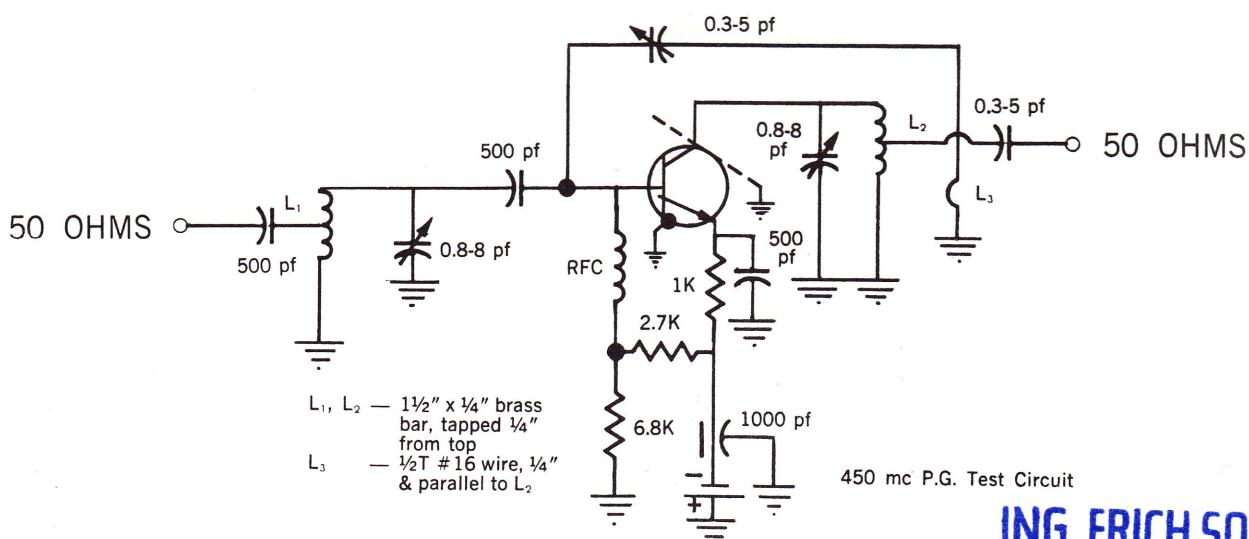
1.14 mw/°C for 25°C Amb.



K5002

K5001

K5003

Test Circuit

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Kmc K5001 K5002 K5003

ELECTRICAL PARAMETERS AT 25°C						K5001			K5002			K5003			
SYMBOL	PARAMETER	TEST CONDITIONS	MIN.	Typ.	MAX.	MIN.	Typ.	MAX.	MIN.	Typ.	MAX.	MIN.	Typ.	MAX.	UNITS
BV CBO	collector-base breakdown	$I_C = 10 \mu A$	25	30	—	25	30	—	25	30	—	volts			
BV EBO	emitter-base breakdown	$I_E = 10 \mu A$	2.5	5	—	2.5	5	—	2.5	5	—	volts			
I_{CBO}	collector cutoff current	$V_{CB} = 15V$	—	.01	.05	—	.01	.05	—	.01	.05	μA			
h_{FE}	current transfer ratio	$I_C = 3mA, V_{CE} = 1V$	20	100	300	20	100	300	20	100	300	—			
C_{ob}	output capacitance NOTE 1	$V_{CB} = 10V$	—	.8	1.0	—	.8	1.0	—	.8	1.0	pf			
G_{pe}	small signal power gain	$f = 450mc, V_{CE} = 6V$ $I_C = .7 ma.$	18	22	—	18	22	—	18	22	—	db			
NF	noise figure (device)	$f = 450 mc, V_{CE} = 6V$ $I_C = .7 ma$	—	1.4	1.5	—	1.7	2.0	—	2.2	2.5	db			
NF	noise figure (device)	$f = 200mc, V_{CE} = 6V$ $I_C = 1 ma$	—	1.0	1.25	—	1.25	1.5	—	1.5	1.75	db			

Note 1: This is a floating measurement. These transistors have an intrinsic feedback capacitance (C_{bc}) of 0.35 pf.
The package capacitance is approximately 0.4 pf.